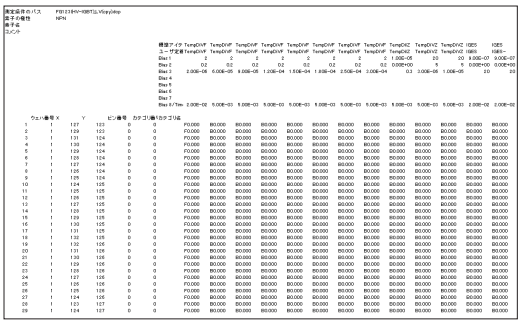
MOS-FET　IGBT　THYRISTOR　DIODE

SEMICONDUCTOR TEST SYSTEM 半導体テストシステム

CHT3012ZZ 3000V 1200A

●CHT3012ZZ is DC measurement tester for power semiconductor which has 3kV-1200A forcing ability. Measurement table in the picture is heat stage and it is possible to rise up temperature to 200℃.

●パワー半導体用のDC測定テスターで、3kV-1200Aの印加能力を持っています。写真の測定台はヒーターステージなっており200℃までの温度上昇が可能です。

MODEL	CHT3012ZZ
SOFTWARE	
TEST PLAN/SORT PLAN	200/100
BIN OUT	24
DC UNIT	
TEST DEVICES	MOS-FET, IGBT, Thyristor, Diode
VOLTAGE/CURRENT	3000V/1200A
TEST ITEMS	
MOS-FET	I_{DSS}, I_{DSR}, I_{GSS+}, I_{GSS-}, BV_{DSS}, BV_{DSR}, V_{FSDS}, VTH, VTH2, V_{DSON}, R_{DSON}, I_{DON}, GMP
IGBT	I_{CES}, $+I_{GES}$, $-I_{GES}$, BV_{CES}, GShock+, GShock-, $+BV_{GES}$, $-BV_{GES}$, VTH, $V_{CE(SAT)}$, V_F, HVTH
THYRISTOR	I_{DRM}, I_{RGM}, V_{RGM}, V_{GFM}, V_{TM}, V_{GT}, I_{GT}, I_H, V_{DRM}
DIODE	I_R, BV_R, V_F
DIMENSIONS & WEIGHT	550(W)×860(D)×1700(H)…240kg

[Indication example of measurement data by log format]
[ログ形式 測定データ表示例]